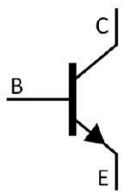


Silicon NPN transistor in a TO-18 Plastic Package.

High V_{CEO} , high f_T .

27MHz CB transceiver driver applications.



PIN1 Emitter PIN 2 Collector PIN 3 Base

/ h

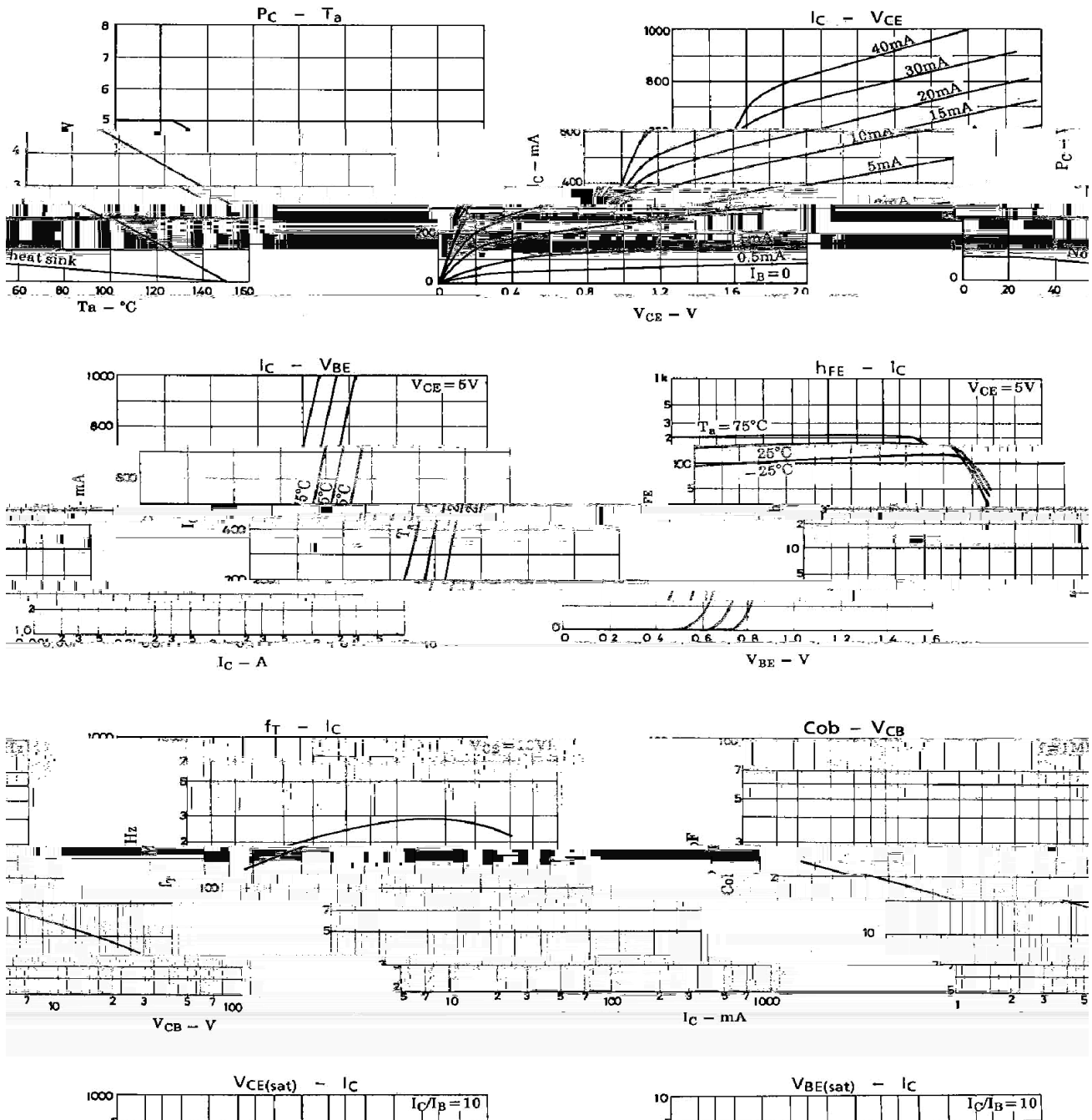
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	75	V
Collector to Emitter Voltage	V_{CER}	75	V
Collector to Emitter Voltage	V_{CEO}	45	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.0	A
Collector Current – Continuous(Pulse)	I_{CP}	1.5	A
Collector Power Dissipation	P_C	0.75	W
Collector Power Dissipation	$P_C(T_C=25)$	5.0	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=10 A \quad I_E=0$	75			V
Collector to Emitter Breakdown Voltage	V_{CER}	$I_C=1.0mA \quad R_{BE}=150$	75			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA \quad I_B=0$	45			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10 A \quad I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=40V \quad I_E=0$			1.0	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=4.0V \quad I_C=0$			1.0	A
DC Current Gain	h_{FE}	$V_{CE}=5.0V \quad I_C=500mA$	60		320	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA \quad I_B=50mA$		0.2	0.6	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=500mA \quad I_B=50mA$		0.9	1.2	V
Transition Frequency	f_T	$V_{CE}=10V \quad I_C=50mA$	180	250		MHz
Reverse Transfer Capacitance	C_{ob}	$V_{CB}=10V \quad f=1.0MHz$		15	25	pF

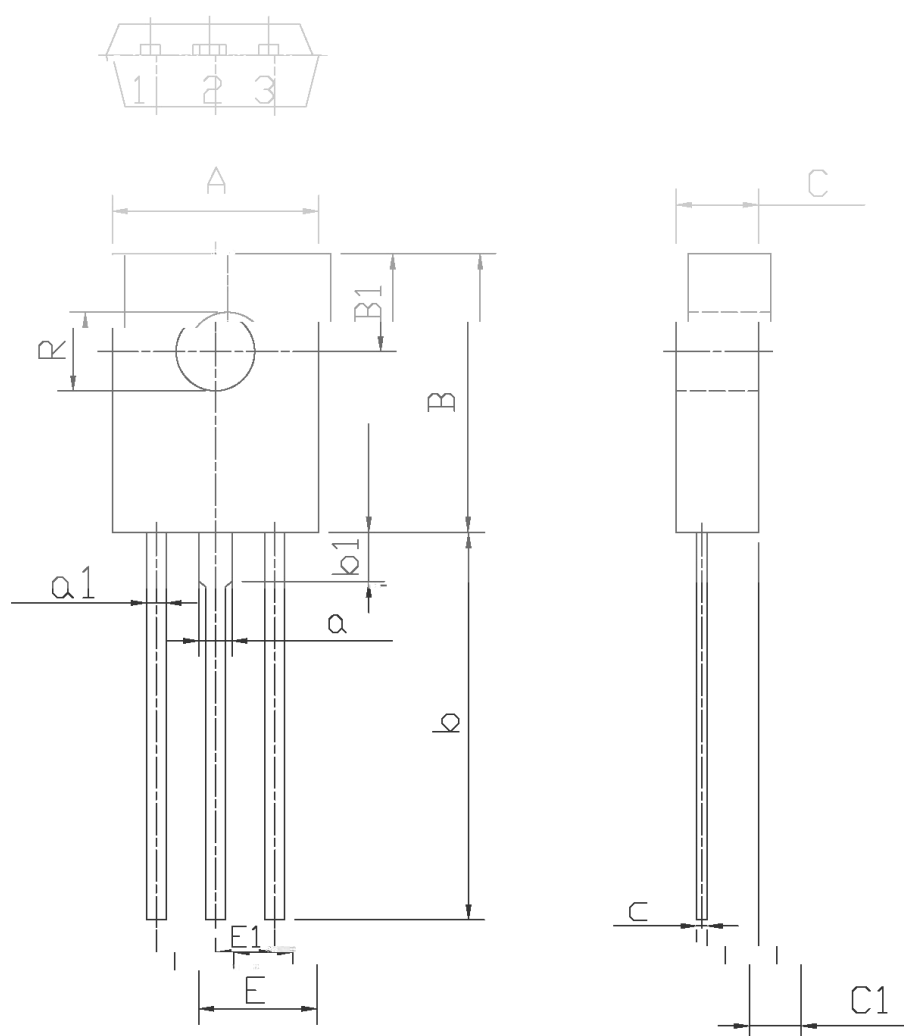
/ Electrical Characteristic Curve



/ Package Dimensions

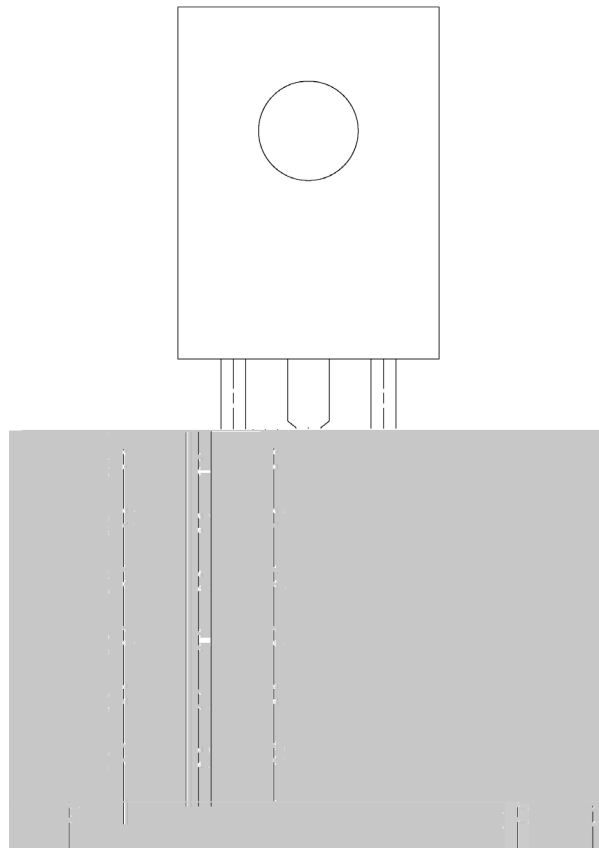
1U-126T

单位: mm

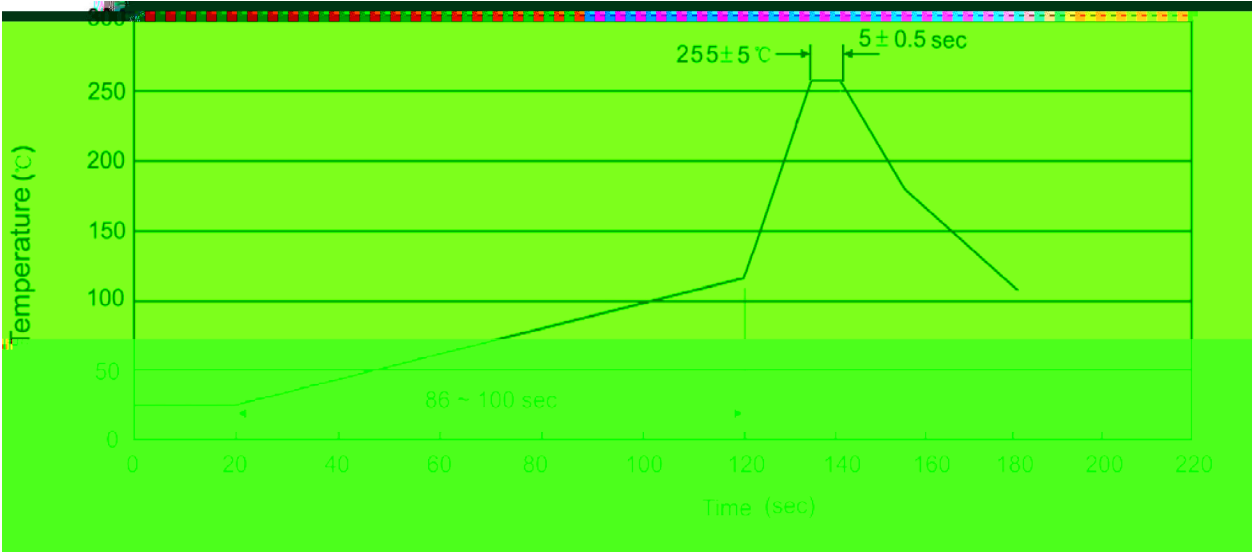


Symbol	Dimensions in Millimeters		Symbol	Dimensions in Millimeters	
	Min	Max		Min	Max
A	7.8	8.2	a1	0.65	0.85
B	10.8	11.2	E	4.4	4.8
B1	3.8	4.2	C	3.1	3.3
R	2.95	3.15	C1	1.9	2.1
b	14	16	c	0.3	0.6
b1	1.9		a	1.27	
E1	2.1	2.5			

/ Marking Instructions



() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-126/F	500	6	3,000	5	15,000	135×190	237×172×102	560×245×195

/ TUBE

Package Type 封装形式	Units 包装数量	Dimension 包装尺寸 (unit: mm ³)
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